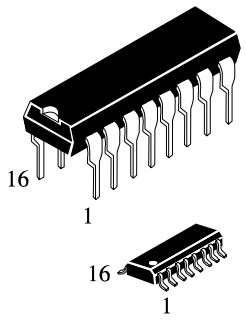
IN74HC367A

Hex 3-State Noninverting Buffer with Separate 2-Bit and 4-Bit Sections

High-Performance Silicon-Gate CMOS



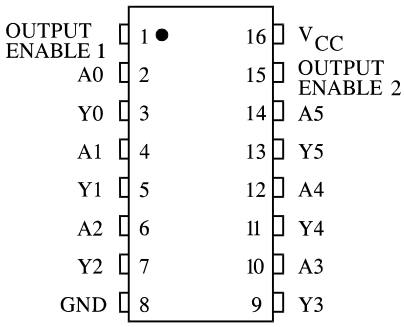
ORDERING INFORMATION
IN74HC367AN Plastic
IN74HC367AD SOIC
T_A = -55° to 125° C for all packages

The IN74HC367A is identical in pinout to the LS/ALS367. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

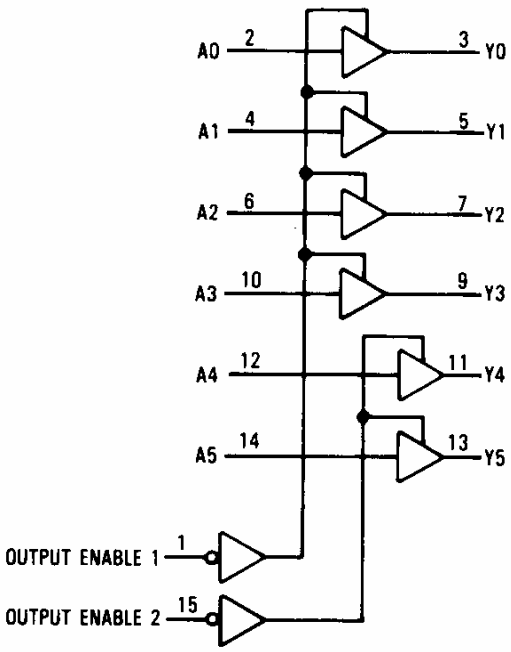
This device is arranged into 2-Bit and 4-Bit sections, each having its own active-low Output Enable. When either of the enables is high, the affected buffer outputs are placed into high-impedance states. The IN74HC367A has noninverting outputs.

- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices

PIN ASSIGNMENT



LOGIC DIAGRAM



PIN 16 =V_{CC}
PIN 8 = GND

FUNCTION TABLE

Inputs		Output
Enable 1,Enable 2	A	Y
L	L	L
L	H	H
H	X	Z

Z = high impedance
X = don't care

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{IN}	DC Input Voltage (Referenced to GND)	-1.5 to V_{CC} +1.5	V
V_{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} +0.5	V
I_{IN}	DC Input Current, per Pin	±20	mA
I_{OUT}	DC Output Current, per Pin	±35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±75	mA
P_D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
Tstg	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.
+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		-55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	V_{CC} =2.0 V V_{CC} =4.5 V V_{CC} =6.0 V	0 0 0	1000 500 400	ns

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND≤(V_{IN} or V_{OUT})≤V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25 °C to -55°C	≤85 °C	≤125 °C	
V_{IH}	Minimum High-Level Input Voltage	V_{OUT}= V_{CC}-0.1 V $\|I_{OUT}\|$ ≤ 20 μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low - Level Input Voltage	V_{OUT}=0.1 V $\|I_{OUT}\|$ ≤ 20 μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V_{OH}	Minimum High-Level Output Voltage	V_{IN}=V_{IH} $\|I_{OUT}\|$ ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{IN}=V_{IH} $\|I_{OUT}\|$ ≤ 6.0 mA $\|I_{OUT}\|$ ≤ 7.8 mA	 4.5 6.0	 3.98 5.48	 3.84 5.34	 3.7 5.2	
V_{OL}	Maximum Low-Level Output Voltage	V_{IN}= V_{IL} $\|I_{OUT}\|$ ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{IN}= V_{IL} $\|I_{OUT}\|$ ≤ 6.0 mA $\|I_{OUT}\|$ ≤ 7.8 mA	 4.5 6.0	 0.26 0.26	 0.33 0.33	 0.4 0.4	
I_{IN}	Maximum Input Leakage Current	V_{IN}=V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V_{IN}= V_{IL} or V_{IH} V_{OUT}=V_{CC} or GND	6.0	±0.5	±5.0	±10	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{IN}=V_{CC} or GND I_{OUT}=0μA	6.0	8.0	80	160	μA

AC ELECTRICAL CHARACTERISTICS (C_L=50pF,Input t_r=t_f=6.0 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25 °C to -55°C	≤85°C	≤125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 4.5 6.0	120 24 20	150 30 26	180 36 31	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay ,Output Enable to Output Y (Figures 2 and 4)	2.0 4.5 6.0	175 35 30	220 44 37	265 53 46	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay ,Output Enable to Output Y (Figures 2 and 4)	2.0 4.5 6.0	190 38 32	240 48 41	285 57 48	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
C_{IN}	Maximum Input Capacitance	-	10	10	10	pF
C_{OUT}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

C_{PD}	Power Dissipation Capacitance (Per Buffer) Used to determine the no-load dynamic power consumption: $P_D=C_{PD}V_{CC}^2f+I_{CC}V_{CC}$	Typical @25°C,V_{CC}=5.0 V 40	pF

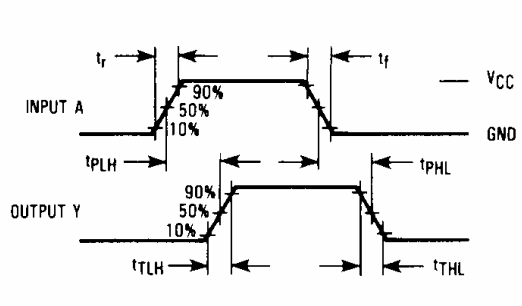


Figure 1. Switching Waveforms

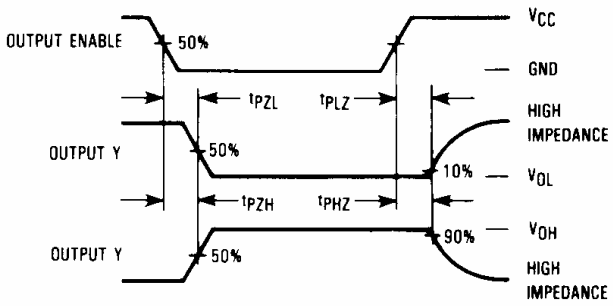


Figure 2. Switching Waveforms

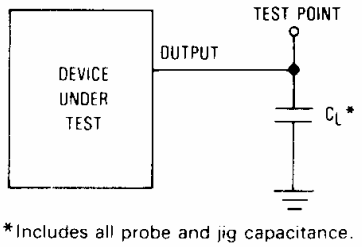


Figure 3. Test Circuit

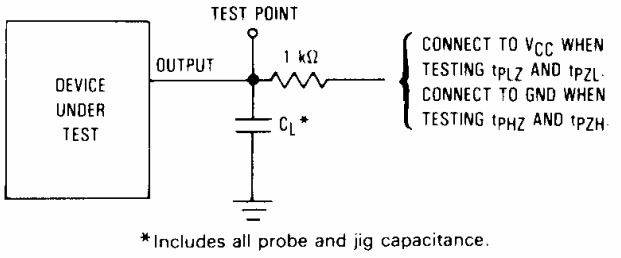
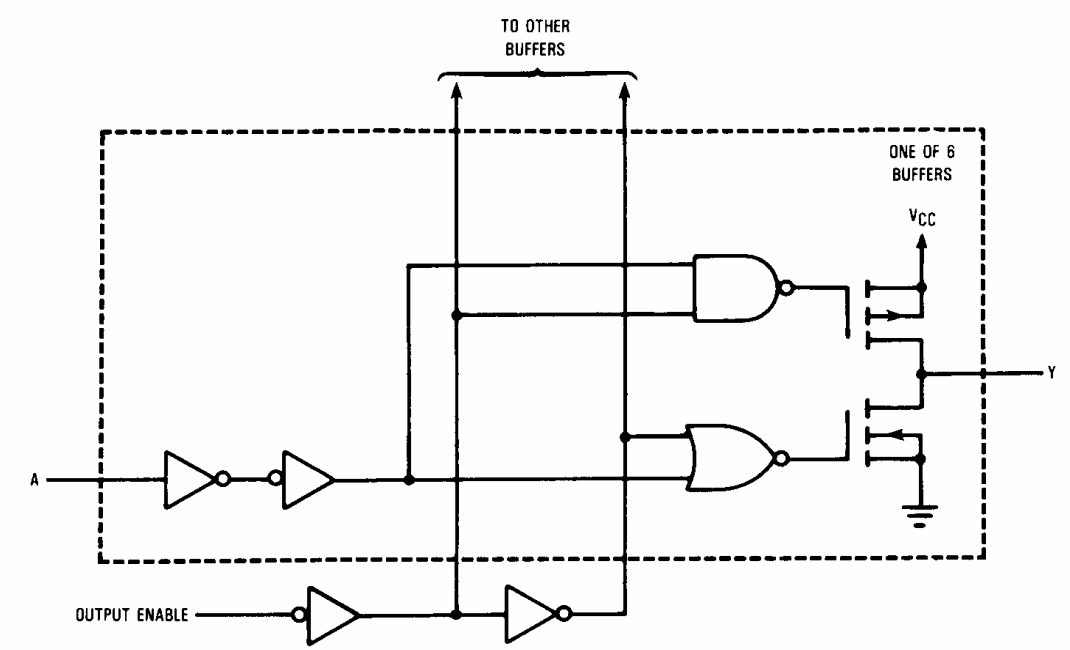


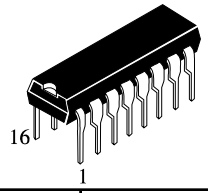
Figure 4. Test Circuit

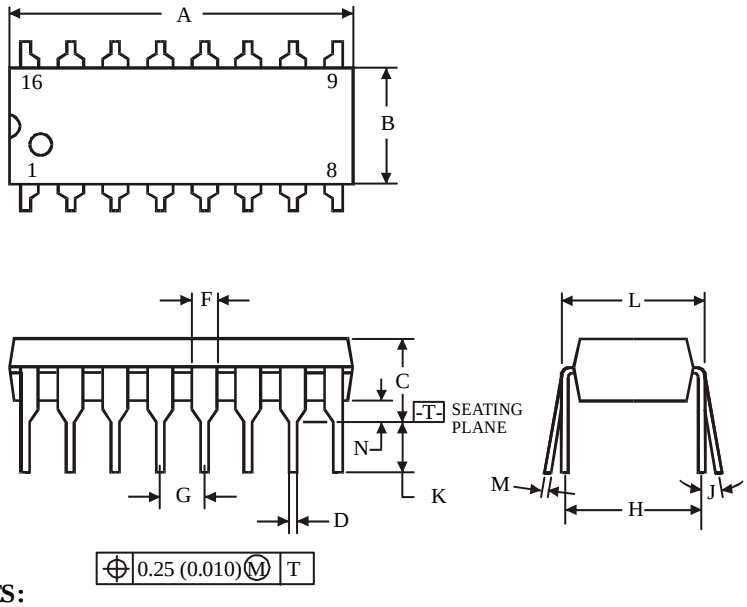
EXPANDED LOGIC DIAGRAM

(1/6 of the Device)



N SUFFIX PLASTIC DIP
(MS - 001BB)



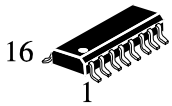


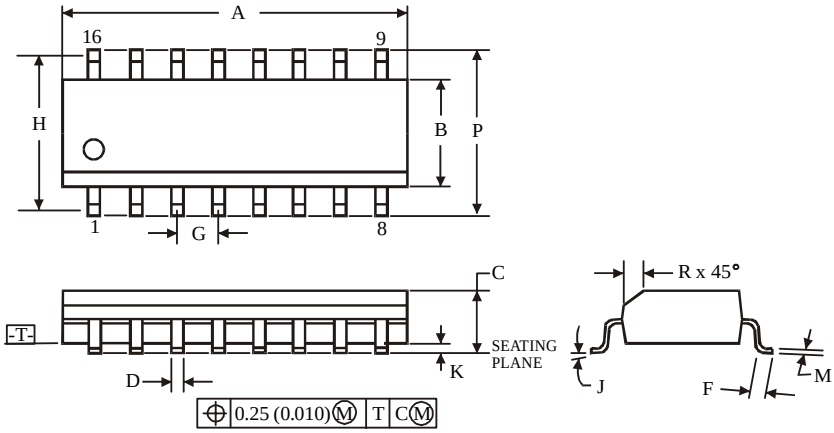
	Dimension, mm	
Symbol	**MIN**	**MAX**
A	18.67	19.69
B	6.1	7.11
C		5.33
D	0.36	0.56
F	1.14	1.78
G	2.54	
H	7.62	
J	0°	10°
K	2.92	3.81
L	7.62	8.26
M	0.2	0.36
N	0.38	

NOTES:

1. Dimensions “A”, “B” do not include mold flash or protrusions.
   Maximum mold flash or protrusions 0.25 mm (0.010) per side.

D SUFFIX SOIC
(MS - 012AC)





	Dimension, mm	
Symbol	**MIN**	**MAX**
A	9.8	10
B	3.8	4
C	1.35	1.75
D	0.33	0.51
F	0.4	1.27
G	1.27	
H	5.72	
J	0°	8°
K	0.1	0.25
M	0.19	0.25
P	5.8	6.2
R	0.25	0.5

NOTES:

1. Dimensions A and B do not include mold flash or protrusion.
2. Maximum mold flash or protrusion 0.15 mm (0.006) per side
   for A; for B – 0.25 mm (0.010) per side.